

Abstracts

A 1.9 GHz single-chip RF front-end GaAs MMIC with low-distortion cascode FET mixer for Personal Handy-phone System terminals (1998 Vol. I [MWSYM])

M. Nakayama, K.-I. Horiguchi, K. Yamamoto, Y. Yoshii, S. Sugiyama, N. Suematsu and T. Takagi. "A 1.9 GHz single-chip RF front-end GaAs MMIC with low-distortion cascode FET mixer for Personal Handy-phone System terminals (1998 Vol. I [MWSYM])." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 171-174.

This paper describes new single-chip RF front-end GaAs MMIC for 1.9 GHz Japanese PHS handheld terminals. The IC consists of a high power amplifier, a T/R switch, a low noise amplifier, a newly developed low distortion cascode FET mixer and a negative voltage generator for FET gate bias voltage. The IC has high performance as an RF front-end for PHS terminals.

 [Return to main document.](#)